



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOD-323 Plastic-Encapsulate Diode

B5817WS SCHOTTKY BARRIER DIODE

FEATURES

Power dissipation

P_D : 200 mW ($T_{amb}=25^{\circ}C$)

Collector current

I_F : 1 A

Collector-base voltage

V_R : 20 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



MARKING: SJ

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 1mA$	20		V
Reverse voltage leakage current	I_R	$V_R = 20V$		1	mA
Forward voltage	V_F	$I_F = 1A$ $I_F = 3A$		0.45 0.75	V
Diode capacitance	C_D	$V_R = 4V, f = 1MHz$		120	pF